

# KSE180

Rev.E Mar.-2016

## / Descriptions

KF \$( ) - = E GE Silicon NPN transistor in a TO-18 Plastic Package.

## / Features

high speed switching.

## / Applications

%  
Power audio amplifier, high speed switching applications.

## / Equivalent Circuit



## / Pinning



PIN1 Emitter      PIN 2 Collector      PIN 3 Base

## / $h_{FE}$ Classifications & Marking

See Marking Instructions.

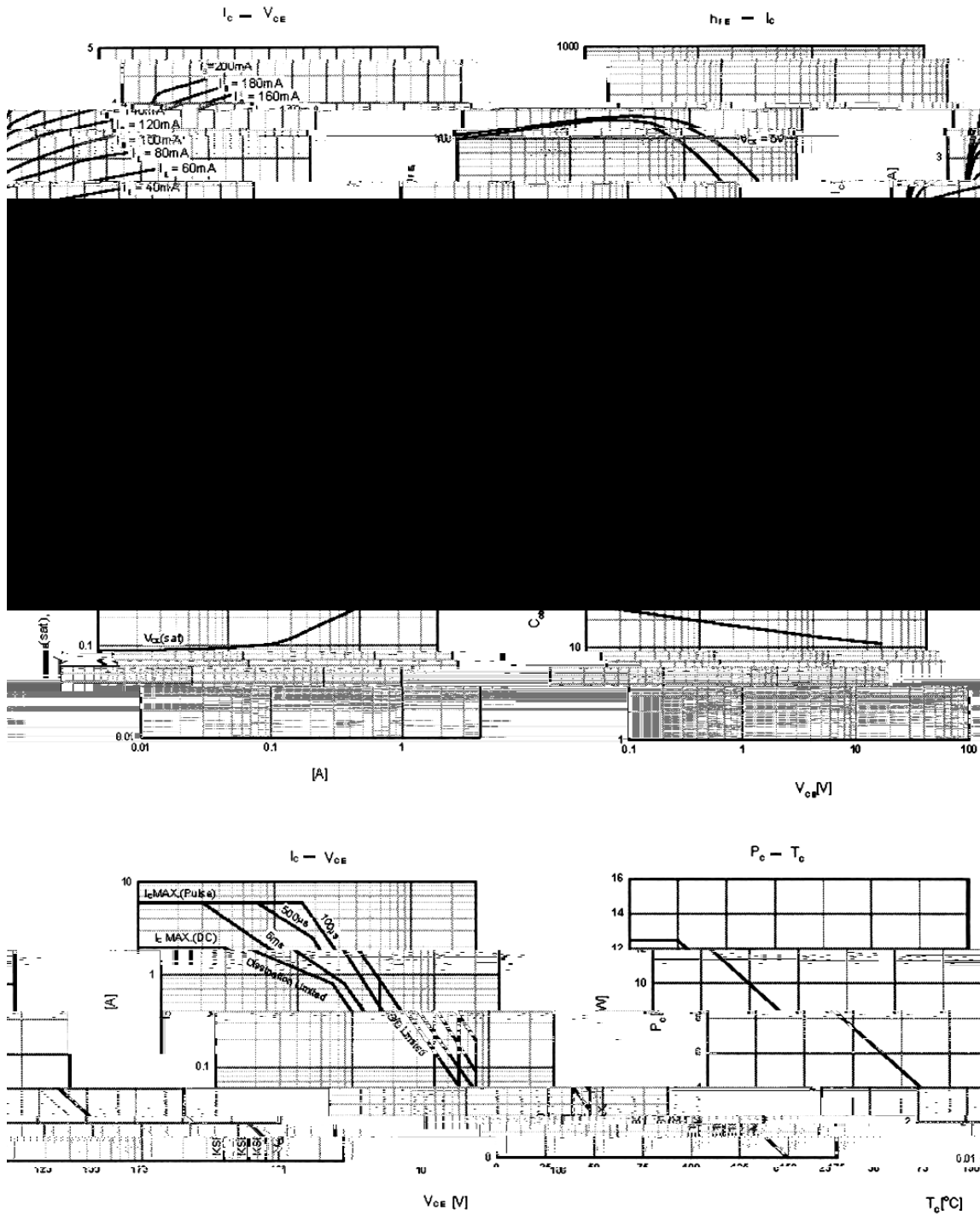
**/ Absolute Maximum Ratings(Ta=25 )**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	60	V
Collector to Emitter Voltage	$V_{CEO}$	40	V
Emitter to Base Voltage	$V_{EBO}$	7.0	V
Collector Current – Continuous	$I_C$	3.0	A
Collector Current – Continuous(Pulse)	$I_{CP}$	6.0	A
Base Current – Continuous	$I_B$	1.0	A
Collector Power Dissipation	$P_C$	1.5	W
Collector Power Dissipation	$P_C(T_C=25 )$	12.5	W
Junction Temperature	$T_j$	150	
Storage Temperature Range	$T_{stg}$	-55 150	

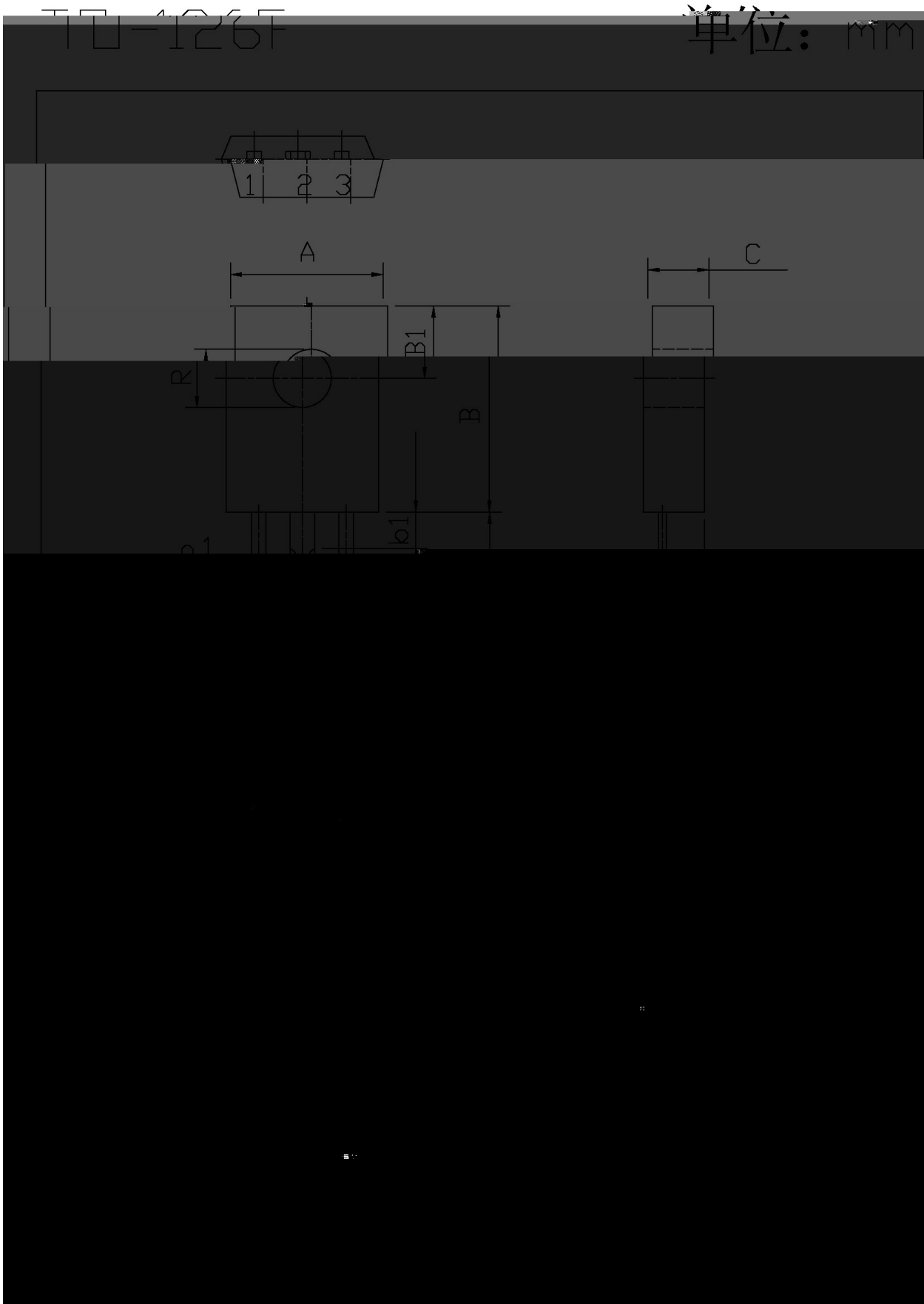
**/ Electrical Characteristics(Ta=25 )**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=10mA$ $I_B=0$	40			V
Collector Cut-Off Current	$I_{CBO(1)}$	$V_{CB}=60V$ $I_B=0$			0.1	$\mu A$
	$I_{CBO(2)}$	$V_{CB}=60V$ $I_E=0$ $T_C=150$			0.1	mA
Emitter Cut-off Current	$I_{EBO}$	$V_{BE}=7.0V$ $I_C=0$			0.1	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=100mA$	50		250	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=1.5A$	12			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=500mA$	30			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=500mA$ $I_B=50mA$			0.3	V
	$V_{CE(sat)(2)}$	$I_C=1.5A$ $I_B=150mA$			0.9	V
	$V_{CE(sat)(3)}$	$I_C=3.0A$ $I_B=600mA$			1.7	V
Base to Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=1.5A$ $I_B=150mA$			1.5	V
	$V_{BE(sat)(2)}$	$I_C=3.0A$ $I_B=600mA$			2.0	V
Base to Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=1.0V$ $I_C=500mA$			1.2	V
Transition Frequency	$f_T$	$V_{CE}=10V$ $I_C=100mA$	50			MHz
Output Capacitance	$C_{ob}$	$V_{CB}=10V$ $f=0.1MHz$ $I_E=0$			30	pF

/ Electrical Characteristic Curve



/ Package Dimensions



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( ) / Temperature Profile for Dip Soldering(Pb-Free)



- |   |        |     |            |        |   |                                      |
|---|--------|-----|------------|--------|---|--------------------------------------|
| 1 | 25     | 150 | 60         | 90sec; | Note:                                     | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 |     | 5..0.5sec; |        | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |                                      |
| 3 |        | 2   | 10         | /sec.  | 3. Cooling Speed: 2~10 /sec.              |                                      |

/ Resistance to Soldering Heat Test Conditions

270..5                      10..1 sec.                      Temp.:270±5                      Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units				Dimension			(unit mm <sup>3</sup> )

/ TUBE

Package Type	Units				Dimension			(unit mm <sup>3</sup> )

/ Notices